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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	133
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p125-pq208i

The absolute maximum junction temperature is 100°C. EQ 1 shows a sample calculation of the absolute maximum power dissipation allowed for a 484-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja}(\text{°C/W})} = \frac{100\text{°C} - 70\text{°C}}{20.5\text{°C/W}} = 1.463\ \text{W}$$

EQ 1

Table 2-5 • **Package Thermal Resistivities**

Package Type	Device	Pin Count	θ_{jc}	θ_{ja}			Units
				Still Air	200 ft/min	500 ft/min	
Quad Flat No Lead	A3P030	132	0.4	21.4	16.8	15.3	°C/W
	A3P060	132	0.3	21.2	16.6	15.0	°C/W
	A3P125	132	0.2	21.1	16.5	14.9	°C/W
	A3P250	132	0.1	21.0	16.4	14.8	°C/W
Very Thin Quad Flat Pack (VQFP)	All devices	100	10.0	35.3	29.4	27.1	°C/W
Thin Quad Flat Pack (TQFP)	All devices	144	11.0	33.5	28.0	25.7	°C/W
Plastic Quad Flat Pack (PQFP)	All devices	208	8.0	26.1	22.5	20.8	°C/W
Fine Pitch Ball Grid Array (FBGA)	See note*	144	3.8	26.9	22.9	21.5	°C/W
	See note*	256	3.8	26.6	22.8	21.5	°C/W
	See note*	484	3.2	20.5	17.0	15.9	°C/W
	A3P1000	144	6.3	31.6	26.2	24.2	°C/W
	A3P1000	256	6.6	28.1	24.4	22.7	°C/W
	A3P1000	484	8.0	23.3	19.0	16.7	°C/W

*Note: *This information applies to all ProASIC3 devices except the A3P1000. Detailed device/package thermal information will be available in future revisions of the datasheet.*

Temperature and Voltage Derating Factors

Table 2-6 • **Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 70°C, VCC = 1.425 V)**

Array Voltage VCC (V)	Junction Temperature (°C)					
	–40°C	0°C	25°C	70°C	85°C	100°C
1.425	0.88	0.93	0.95	1.00	1.02	1.04
1.500	0.83	0.88	0.90	0.95	0.96	0.98
1.575	0.80	0.84	0.87	0.91	0.93	0.94

Calculating Power Dissipation

Quiescent Supply Current

Table 2-7 • Quiescent Supply Current Characteristics

	A3P015	A3P030	A3P060	A3P125	A3P250	A3P400	A3P600	A3P1000
Typical (25°C)	2 mA	2 mA	2 mA	2 mA	3 mA	3 mA	5 mA	8 mA
Max. (Commercial)	10 mA	10 mA	10 mA	10 mA	20 mA	20 mA	30 mA	50 mA
Max. (Industrial)	15 mA	15 mA	15 mA	15 mA	30 mA	30 mA	45 mA	75 mA

Note: IDD Includes VCC, VPUMP, VCCI, and VMV currents. Values do not include I/O static contribution, which is shown in Table 2-11 and Table 2-12 on page 2-9.

Power per I/O Pin

Table 2-8 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Advanced I/O Banks

	VMV (V)	Static Power P_{DC2} (mW) [1]	Dynamic Power PAC9 (µW/MHz) [2]
Single-Ended			
3.3 V LVTTL / 3.3 V LVCMOS	3.3	–	16.22
3.3 V LVCMOS Wide Range[3]	3.3	–	16.22
2.5 V LVCMOS	2.5	–	5.12
1.8 V LVCMOS	1.8	–	2.13
1.5 V LVCMOS (JESD8-11)	1.5	–	1.45
3.3 V PCI	3.3	–	18.11
3.3 V PCI-X	3.3	–	18.11
Differential			
LVDS	2.5	2.26	1.20
LVPECL	3.3	5.72	1.87

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-9 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Standard Plus I/O Banks

	VMV (V)	Static Power PDC2 (mW) [1]	Dynamic Power PAC9 (µW/MHz) [2]
Single-Ended			
3.3 V LVTTL / 3.3 V LVCMOS	3.3	–	16.23
3.3 V LVCMOS Wide Range[3]	3.3	–	16.23

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-9 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Standard Plus I/O Banks

	VMV (V)	Static Power PDC2 (mW) [1]	Dynamic Power PAC9 (µW/MHz) [2]
2.5 V LVCMOS	2.5	–	5.14
1.8 V LVCMOS	1.8	–	2.13
1.5 V LVCMOS (JESD8-11)	1.5	–	1.48
3.3 V PCI	3.3	–	18.13
3.3 V PCI-X	3.3	–	18.13

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

Table 2-10 • Summary of I/O Input Buffer Power (Per Pin) – Default I/O Software Settings Applicable to Standard I/O Banks

	VMV (V)	Static Power PDC2 (mW) [1]	Dynamic Power PAC9 (µW/MHz) [2]
Single-Ended			
3.3 V LVTTL / 3.3 V LVCMOS	3.3	–	17.24
3.3 V LVCMOS Wide Range[3]	3.3	–	17.24
2.5 V LVCMOS	2.5	–	5.19
1.8 V LVCMOS	1.8	–	2.18
1.5 V LVCMOS (JESD8-11)	1.5	–	1.52

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

I/O DC Characteristics

Table 2-27 • **Input Capacitance**

Symbol	Definition	Conditions	Min	Max	Units
C_{IN}	Input capacitance	VIN = 0, f = 1.0 MHz	–	8	pF
C_{INCLK}	Input capacitance on the clock pin	VIN = 0, f = 1.0 MHz	–	8	pF

Table 2-28 • **I/O Output Buffer Maximum Resistances[1]**
Applicable to Advanced I/O Banks

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
3.3 V LVCMOS Wide Range[4]	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at http://www.microsemi.com/soc/download/ibis/default.aspx.*
2. *$R_{(PULL\text{-}DOWN\text{-}MAX)}$ = (VOLspec) / IOLspec*
3. *$R_{(PULL\text{-}UP\text{-}MAX)}$ = (VCCImax – VOHspec) / IOHspec*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*

Table 2-39 • Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA[3]	Max mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *I_{IH} is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

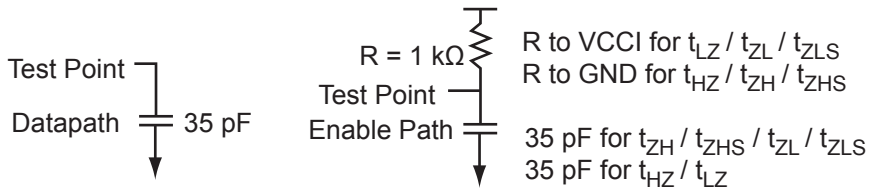


Figure 2-7 • AC Loading

Table 2-40 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	1.4	35

*Note: *Measuring point = Vtrip. See Table 2-22 on page 2-22 for a complete table of trip points.*

Table 2-58 • Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max., V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.7	1.7	3.6	0.7	1.7	2	2	16	18	10	10
4 mA	–0.3	0.7	1.7	3.6	0.7	1.7	4	4	16	18	10	10
6 mA	–0.3	0.7	1.7	3.6	0.7	1.7	6	6	32	37	10	10
8 mA	–0.3	0.7	1.7	3.6	0.7	1.7	8	8	32	37	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

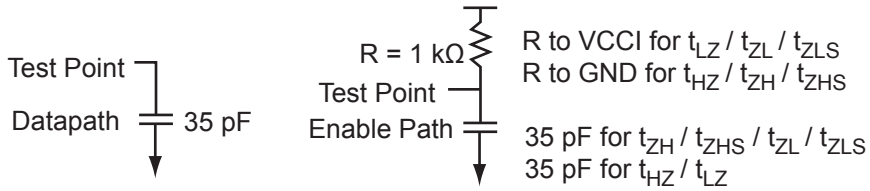


Figure 2-8 • AC Loading

Table 2-59 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	2.5	1.2	35

*Note: *Measuring point = Vtrip. See Table 2-22 on page 2-22 for a complete table of trip points.*

Table 2-64 • 2.5 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	8.20	0.04	1.29	0.43	7.24	8.20	2.03	1.91	ns
	–1	0.56	6.98	0.04	1.10	0.36	6.16	6.98	1.73	1.62	ns
	–2	0.49	6.13	0.03	0.96	0.32	5.41	6.13	1.52	1.43	ns
4 mA	Std.	0.66	8.20	0.04	1.29	0.43	7.24	8.20	2.03	1.91	ns
	–1	0.56	6.98	0.04	1.10	0.36	6.16	6.98	1.73	1.62	ns
	–2	0.49	6.13	0.03	0.96	0.32	5.41	6.13	1.52	1.43	ns
6 mA	Std.	0.66	4.77	0.04	1.29	0.43	4.55	4.77	2.38	2.55	ns
	–1	0.56	4.05	0.04	1.10	0.36	3.87	4.05	2.03	2.17	ns
	–2	0.49	3.56	0.03	0.96	0.32	3.40	3.56	1.78	1.91	ns
8 mA	Std.	0.66	4.77	0.04	1.29	0.43	4.55	4.77	2.38	2.55	ns
	–1	0.56	4.05	0.04	1.10	0.36	3.87	4.05	2.03	2.17	ns
	–2	0.49	3.56	0.03	0.96	0.32	3.40	3.56	1.78	1.91	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-65 • 2.5 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	11.00	0.04	1.29	0.43	10.37	11.00	2.03	1.83	ns
	–1	0.56	9.35	0.04	1.10	0.36	8.83	9.35	1.73	1.56	ns
	–2	0.49	8.21	0.03	0.96	0.32	7.75	8.21	1.52	1.37	ns
4 mA	Std.	0.66	11.00	0.04	1.29	0.43	10.37	11.00	2.03	1.83	ns
	–1	0.56	9.35	0.04	1.10	0.36	8.83	9.35	1.73	1.56	ns
	–2	0.49	8.21	0.03	0.96	0.32	7.75	8.21	1.52	1.37	ns
6 mA	Std.	0.66	7.50	0.04	1.29	0.43	7.36	7.50	2.39	2.46	ns
	–1	0.56	6.38	0.04	1.10	0.36	6.26	6.38	2.03	2.10	ns
	–2	0.49	5.60	0.03	0.96	0.32	5.49	5.60	1.78	1.84	ns
8 mA	Std.	0.66	7.50	0.04	1.29	0.43	7.36	7.50	2.39	2.46	ns
	–1	0.56	6.38	0.04	1.10	0.36	6.26	6.38	2.03	2.10	ns
	–2	0.49	5.60	0.03	0.96	0.32	5.49	5.60	1.78	1.84	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-73 • 1.8 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	14.80	0.04	1.20	0.43	13.49	14.80	2.25	1.46	15.73	17.04	ns
	–1	0.56	12.59	0.04	1.02	0.36	11.48	12.59	1.91	1.25	13.38	14.49	ns
	–2	0.49	11.05	0.03	0.90	0.32	10.08	11.05	1.68	1.09	11.75	12.72	ns
4 mA	Std.	0.66	9.90	0.04	1.20	0.43	9.73	9.90	2.65	2.50	11.97	12.13	ns
	–1	0.56	8.42	0.04	1.02	0.36	8.28	8.42	2.26	2.12	10.18	10.32	ns
	–2	0.49	7.39	0.03	0.90	0.32	7.27	7.39	1.98	1.86	8.94	9.06	ns
6 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	–1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	–2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns
8 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	–1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	–2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-74 • 1.8 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	11.21	0.04	1.20	0.43	8.53	11.21	1.99	1.21	ns
	–1	0.56	9.54	0.04	1.02	0.36	7.26	9.54	1.69	1.03	ns
	–2	0.49	8.37	0.03	0.90	0.32	6.37	8.37	1.49	0.90	ns
4 mA	Std.	0.66	6.34	0.04	1.20	0.43	5.38	6.34	2.41	2.48	ns
	–1	0.56	5.40	0.04	1.02	0.36	4.58	5.40	2.05	2.11	ns
	–2	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

Table 2-86 • Minimum and Maximum DC Input and Output Levels

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max,. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
Per PCI specification	Per PCI curves										10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in Figure 2-11.

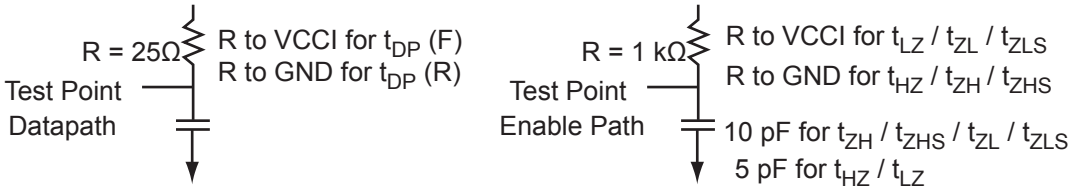


Figure 2-11 • AC Loading

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in Table 2-87.

Table 2-87 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	0.285 * VCCI for $t_{DP(R)}$ 0.615 * VCCI for $t_{DP(F)}$	10

*Note: *Measuring point = V_{trip}. See Table 2-22 on page 2-22 for a complete table of trip points.*

Input Register

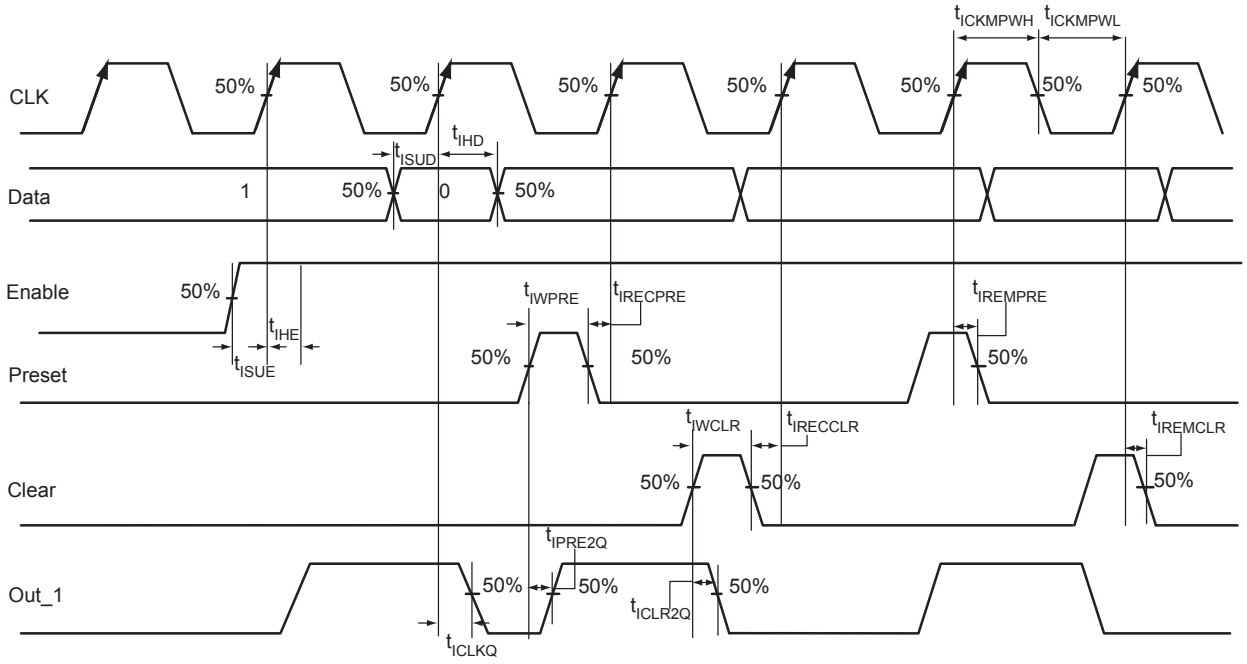


Figure 2-17 • **Input Register Timing Diagram**

Timing Characteristics

Table 2-98 • **Input Data Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.24	0.27	0.32	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.26	0.30	0.35	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.37	0.42	0.50	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.45	0.52	0.61	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	0.00	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	0.00	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width High for the Input Data Register	0.36	0.41	0.48	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width Low for the Input Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Output Register

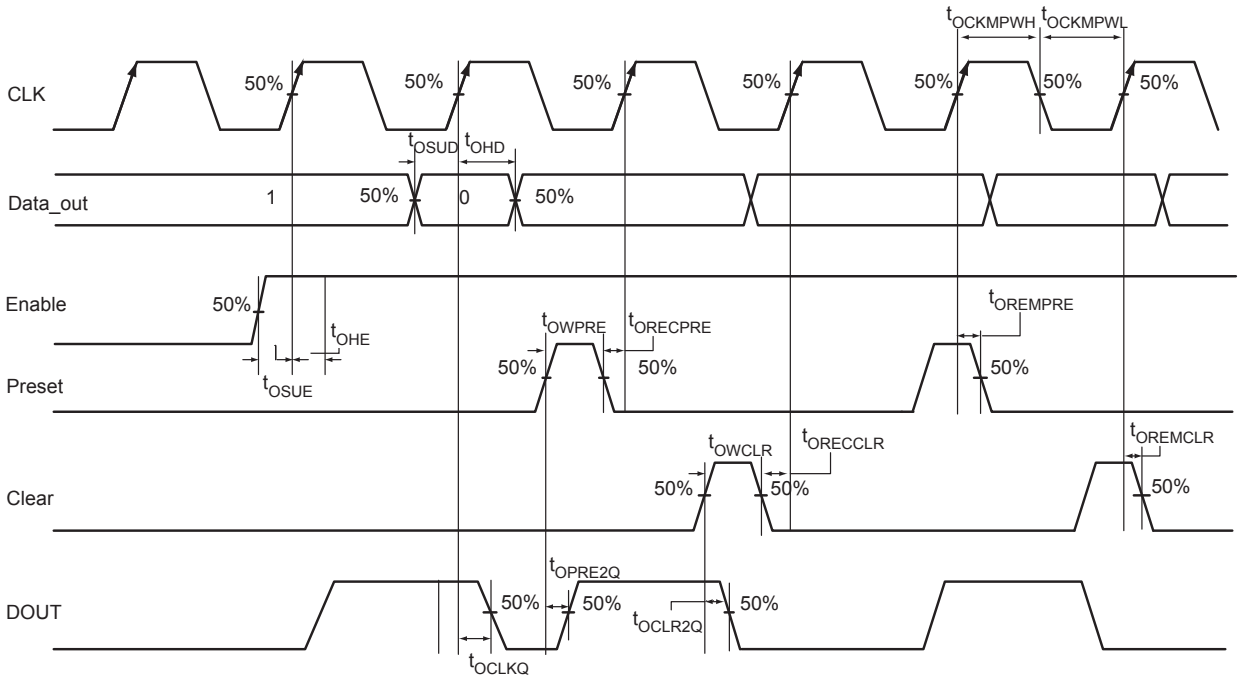


Figure 2-18 • **Output Register Timing Diagram**

Timing Characteristics

Table 2-99 • **Output Data Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.59	0.67	0.79	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.31	0.36	0.42	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OSUE}	Enable Setup Time for the Output Data Register	0.44	0.50	0.59	ns
t_{OHE}	Enable Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.80	0.91	1.07	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.80	0.91	1.07	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.36	0.41	0.48	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

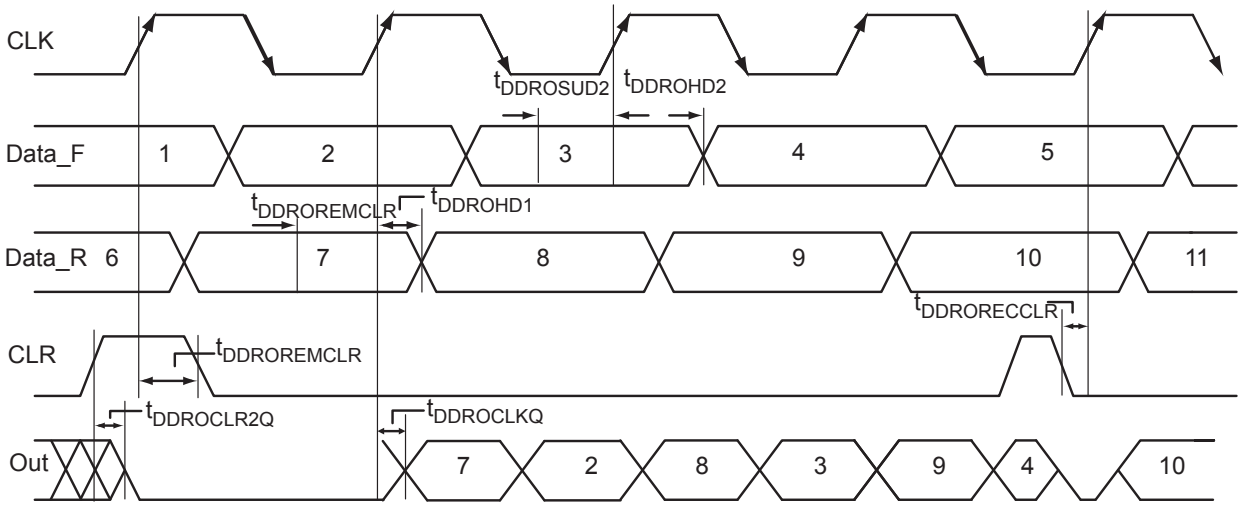


Figure 2-23 • **Output DDR Timing Diagram**

Timing Characteristics

Table 2-104 • **Output DDR Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
$t_{DDROCLKQ}$	Clock-to-Out of DDR for Output DDR	0.70	0.80	0.94	ns
$t_{DDROSUD1}$	Data_F Data Setup for Output DDR	0.38	0.43	0.51	ns
$t_{DDROSUD2}$	Data_R Data Setup for Output DDR	0.38	0.43	0.51	ns
$t_{DDROHD1}$	Data_F Data Hold for Output DDR	0.00	0.00	0.00	ns
$t_{DDROHD2}$	Data_R Data Hold for Output DDR	0.00	0.00	0.00	ns
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out for Output DDR	0.80	0.91	1.07	ns
$t_{DDROREMCLR}$	Asynchronous Clear Removal Time for Output DDR	0.00	0.00	0.00	ns
$t_{DDRORECCLR}$	Asynchronous Clear Recovery Time for Output DDR	0.22	0.25	0.30	ns
$t_{DDROWCLR1}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.22	0.25	0.30	ns
$t_{DDROCKMPWH}$	Clock Minimum Pulse Width High for the Output DDR	0.36	0.41	0.48	ns
$t_{DDROCKMPWL}$	Clock Minimum Pulse Width Low for the Output DDR	0.32	0.37	0.43	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	350	309	263	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The ProASIC3 library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the *Fusion, IGLOO®/e, and ProASIC3/E Macro Library Guide*.

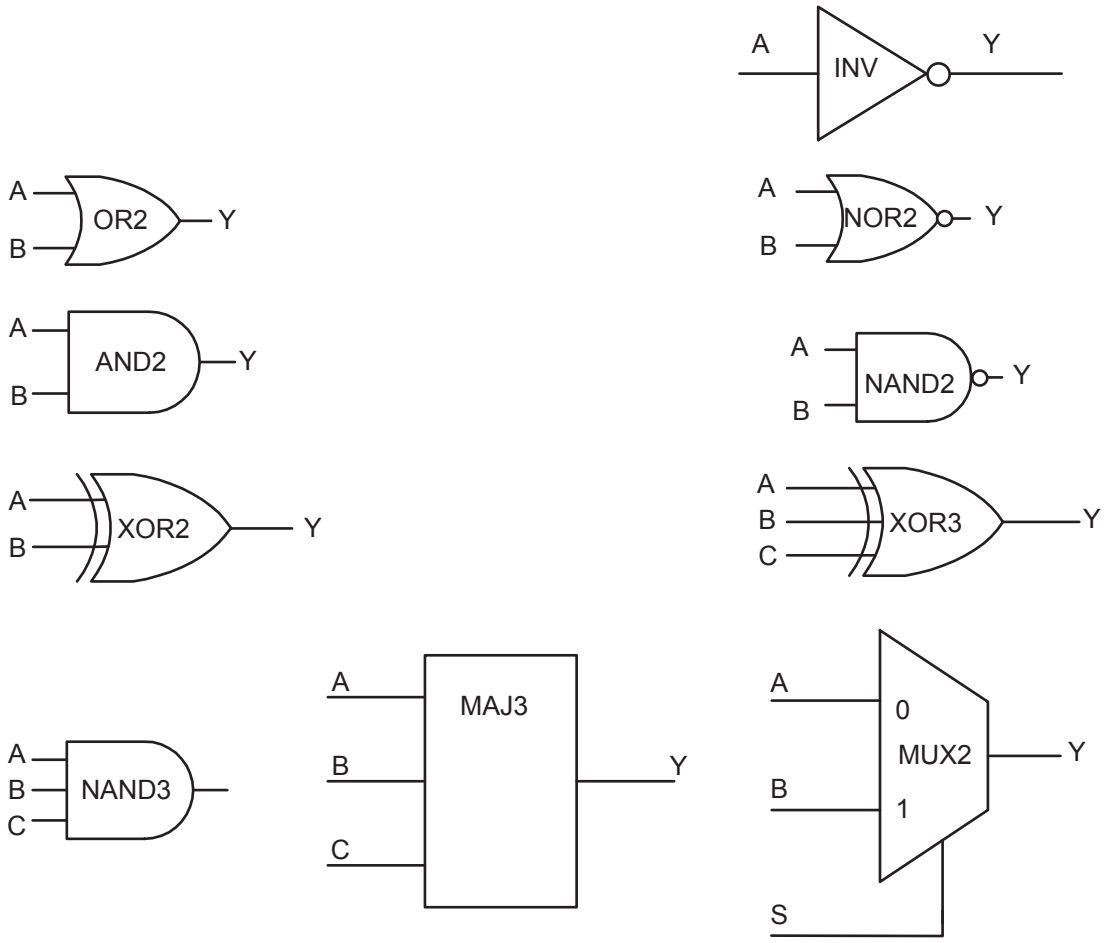


Figure 2-24 • **Sample of Combinatorial Cells**

Embedded SRAM and FIFO Characteristics

SRAM

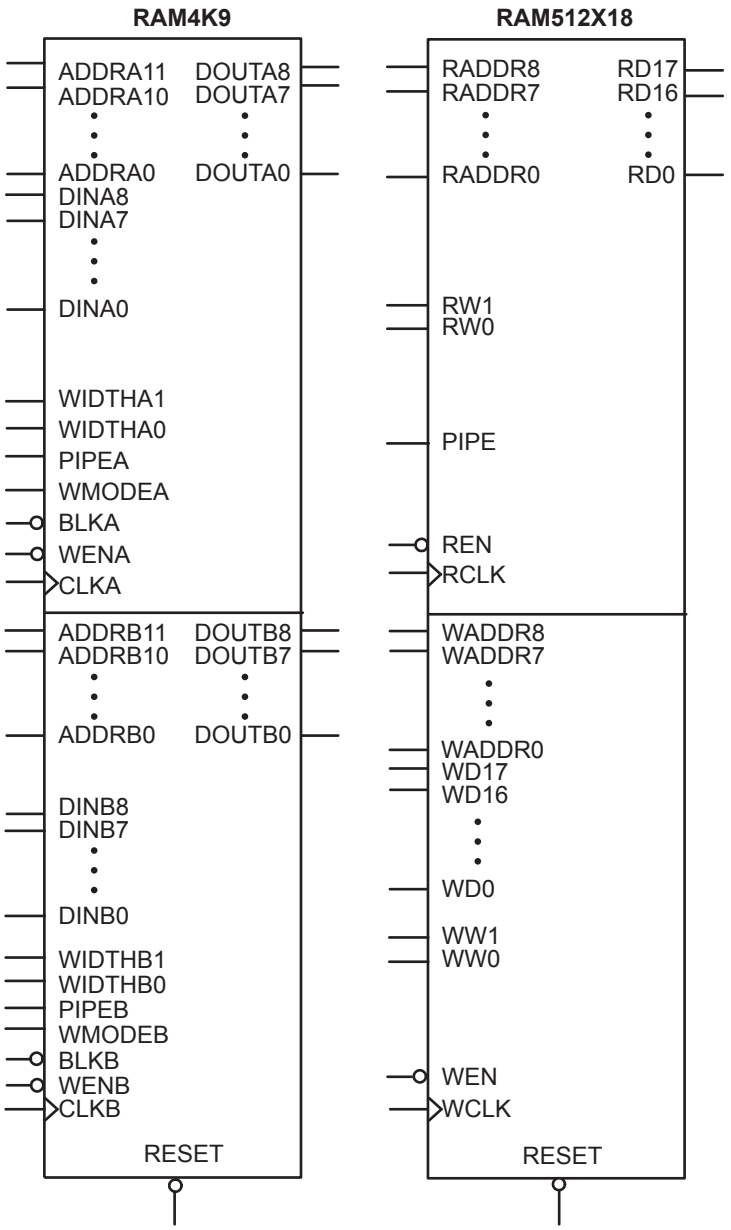


Figure 2-30 • **RAM Models**

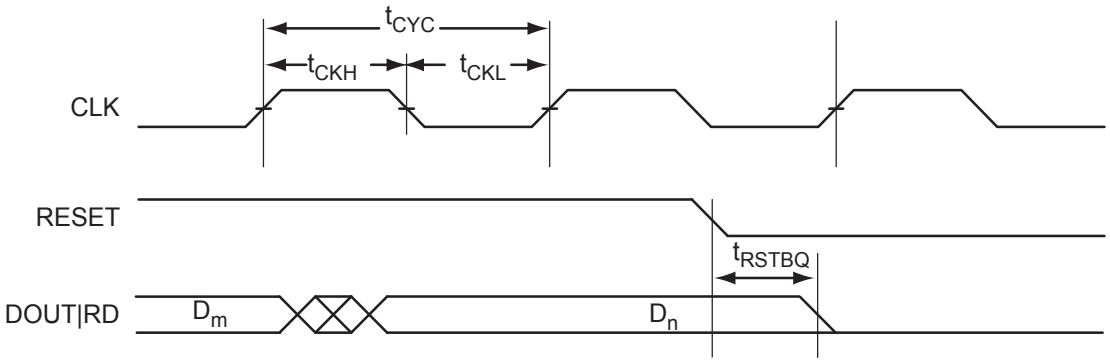


Figure 2-35 • **RAM Reset. Applicable to Both RAM4K9 and RAM512x18.**

QN68	
Pin Number	**A3P030 Function**
1	IO82RSB1
2	IO80RSB1
3	IO78RSB1
4	IO76RSB1
5	GEC0/IO73RSB1
6	GEA0/IO72RSB1
7	GEB0/IO71RSB1
8	VCC
9	GND
10	VCCIB1
11	IO68RSB1
12	IO67RSB1
13	IO66RSB1
14	IO65RSB1
15	IO64RSB1
16	IO63RSB1
17	IO62RSB1
18	IO60RSB1
19	IO58RSB1
20	IO56RSB1
21	IO54RSB1
22	IO52RSB1
23	IO51RSB1
24	VCC
25	GND
26	VCCIB1
27	IO50RSB1
28	IO48RSB1
29	IO46RSB1
30	IO44RSB1
31	IO42RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP
36	TDO

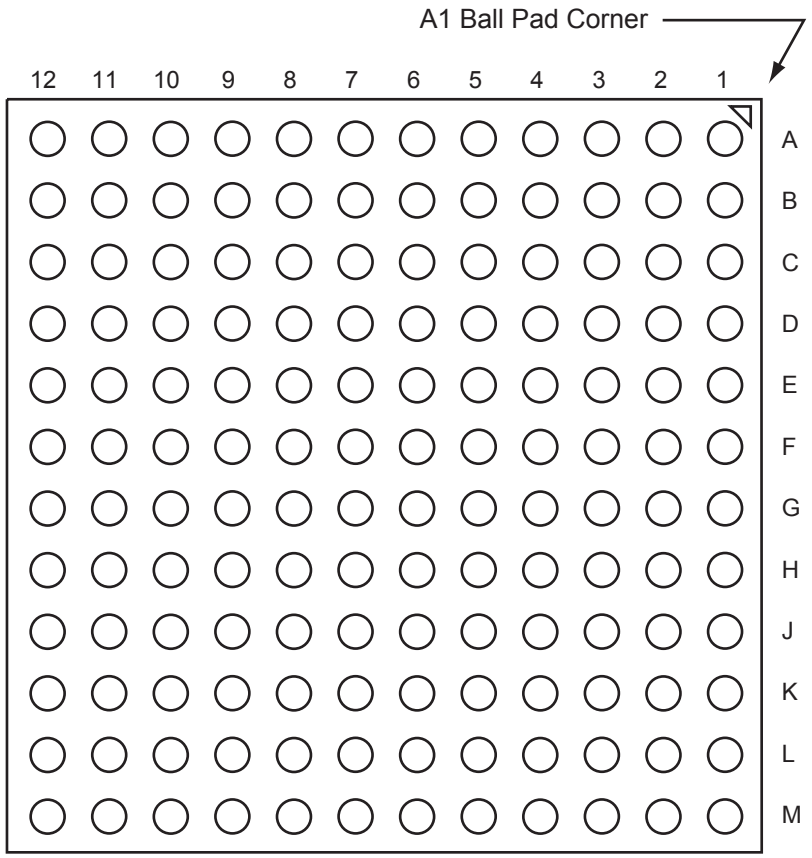
QN68	
Pin Number	**A3P030 Function**
37	TRST
38	VJTAG
39	IO40RSB0
40	IO37RSB0
41	GDB0/IO34RSB0
42	GDA0/IO33RSB0
43	GDC0/IO32RSB0
44	VCCIB0
45	GND
46	VCC
47	IO31RSB0
48	IO29RSB0
49	IO28RSB0
50	IO27RSB0
51	IO25RSB0
52	IO24RSB0
53	IO22RSB0
54	IO21RSB0
55	IO19RSB0
56	IO17RSB0
57	IO15RSB0
58	IO14RSB0
59	VCCIB0
60	GND
61	VCC
62	IO12RSB0
63	IO10RSB0
64	IO08RSB0
65	IO06RSB0
66	IO04RSB0
67	IO02RSB0
68	IO00RSB0

PQ208 – Top View

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

FG144 – Bottom View



Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

FG144	
Pin Number	A3P250 Function
A1	GNDQ
A2	VMV0
A3	GAB0/IO02RSB0
A4	GAB1/IO03RSB0
A5	IO16RSB0
A6	GND
A7	IO29RSB0
A8	VCC
A9	IO33RSB0
A10	GBA0/IO39RSB0
A11	GBA1/IO40RSB0
A12	GNDQ
B1	GAB2/IO117UDB3
B2	GND
B3	GAA0/IO00RSB0
B4	GAA1/IO01RSB0
B5	IO14RSB0
B6	IO19RSB0
B7	IO22RSB0
B8	IO30RSB0
B9	GBB0/IO37RSB0
B10	GBB1/IO38RSB0
B11	GND
B12	VMV1
C1	IO117VDB3
C2	GFA2/IO107PPB3
C3	GAC2/IO116UDB3
C4	VCC
C5	IO12RSB0
C6	IO17RSB0
C7	IO24RSB0
C8	IO31RSB0
C9	IO34RSB0
C10	GBA2/IO41PDB1
C11	IO41NDB1
C12	GBC2/IO43PPB1

FG144	
Pin Number	A3P250 Function
D1	IO112NDB3
D2	IO112PDB3
D3	IO116VDB3
D4	GAA2/IO118UPB3
D5	GAC0/IO04RSB0
D6	GAC1/IO05RSB0
D7	GBC0/IO35RSB0
D8	GBC1/IO36RSB0
D9	GBB2/IO42PDB1
D10	IO42NDB1
D11	IO43NPB1
D12	GCB1/IO49PPB1
E1	VCC
E2	GFC0/IO110NDB3
E3	GFC1/IO110PDB3
E4	VCCIB3
E5	IO118VPB3
E6	VCCIB0
E7	VCCIB0
E8	GCC1/IO48PDB1
E9	VCCIB1
E10	VCC
E11	GCA0/IO50NDB1
E12	IO51NDB1
F1	GFB0/IO109NPB3
F2	VCOMPLF
F3	GFB1/IO109PPB3
F4	IO107NPB3
F5	GND
F6	GND
F7	GND
F8	GCC0/IO48NDB1
F9	GCB0/IO49NPB1
F10	GND
F11	GCA1/IO50PDB1
F12	GCA2/IO51PDB1

FG144	
Pin Number	A3P250 Function
G1	GFA1/IO108PPB3
G2	GND
G3	VCCPLF
G4	GFA0/IO108NPB3
G5	GND
G6	GND
G7	GND
G8	GDC1/IO58UPB1
G9	IO53NDB1
G10	GCC2/IO53PDB1
G11	IO52NDB1
G12	GCB2/IO52PDB1
H1	VCC
H2	GFB2/IO106PDB3
H3	GFC2/IO105PSB3
H4	GEC1/IO100PDB3
H5	VCC
H6	IO79RSB2
H7	IO65RSB2
H8	GDB2/IO62RSB2
H9	GDC0/IO58VPB1
H10	VCCIB1
H11	IO54PSB1
H12	VCC
J1	GEB1/IO99PDB3
J2	IO106NDB3
J3	VCCIB3
J4	GEC0/IO100NDB3
J5	IO88RSB2
J6	IO81RSB2
J7	VCC
J8	TCK
J9	GDA2/IO61RSB2
J10	TDO
J11	GDA1/IO60UDB1
J12	GDB1/IO59UDB1

Revision	Changes	Page
Advance v0.6 (continued)	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25
	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	The "Introduction" of the "Advanced I/Os" section was updated.	2-28
	The "I/O Banks" section is new. This section explains the following types of I/Os: Advanced Standard+ Standard Table 2-12 • Automotive ProASIC3 Bank Types Definition and Differences is new. This table describes the standards listed above.	2-29
	PCI-X 3.3 V was added to the Compatible Standards for 3.3 V in Table 2-11 • VCCI Voltages and Compatible Standards	2-29
	Table 2-13 • ProASIC3 I/O Features was updated.	2-30
	The "Double Data Rate (DDR) Support" section was updated to include information concerning implementation of the feature.	2-32
	The "Electrostatic Discharge (ESD) Protection" section was updated to include testing information.	2-35
	Level 3 and 4 descriptions were updated in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices.	2-64
	The notes in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices were updated.	2-64
	The "Simultaneous Switching Outputs (SSOs) and Printed Circuit Board Layout" section is new.	2-41
	A footnote was added to Table 2-14 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in Automotive ProASIC3 Devices (maximum drive strength and high slew selected).	2-30
	Table 2-18 • Automotive ProASIC3 I/O Attributes vs. I/O Standard Applications	2-45
	Table 2-50 • ProASIC3 Output Drive (OUT_DRIVE) for Standard I/O Bank Type (A3P030 device)	2-83
	Table 2-51 • ProASIC3 Output Drive for Standard+ I/O Bank Type was updated.	2-84
	Table 2-54 • ProASIC3 Output Drive for Advanced I/O Bank Type was updated.	2-84
	The "x" was updated in the "User I/O Naming Convention" section.	2-48
	The "VCC Core Supply Voltage" pin description was updated.	2-50
	The "VMVx I/O Supply Voltage (quiet)" pin description was updated to include information concerning leaving the pin unconnected.	2-50
	The "VJTAG JTAG Supply Voltage" pin description was updated.	2-50
	The "VPUMP Programming Supply Voltage" pin description was updated to include information on what happens when the pin is tied to ground.	2-50
	The "I/O User Input/Output" pin description was updated to include information on what happens when the pin is unused.	2-50
	The "JTAG Pins" section was updated to include information on what happens when the pin is unused.	2-51